

Notice of References Cited	Application/Control No. 10/527,202		Applicant(s)/Patent Under Reexamination ITANO ET AL.	
	Examiner TabassomT Tadayyon-Eslami		Art Unit 1709	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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*	B	US-5,120,605	06-1992	Zuel et al.	428/410
*	C	US-2003/0160026	08-2003	Klein et al.	216/83
*	D	US-6,254,796	07-2001	Rath et al.	216/87
*	E	US-3,438,799	04-1969	EMMERICHS GERHARD THEODOR; et. al.	427/327
*	F	US-4,124,516	11-1978	Shinozaki et al.	252/79.2
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*	J	US-2003/0235985	12-2003	Christenson et al.	438/689
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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.